



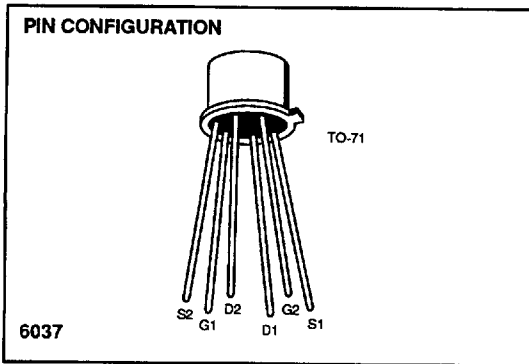
Monolithic Dual N-Channel JFET General Purpose Amplifier

T-27-27

2N3921 / 2N3922

FEATURES

- Low Drain Current
- High Output Impedance
- Matched V_{GS} , ΔV_{GS} and g_{fs}



ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Gate-Source or Gate-Drain Voltage (Note 1)	-50V
Gate Current (Note 1)	50mA
Storage Temperature Range	-65°C to +200°C
Operating Temperature Range	-55°C to +200°C
Load Temperature (Soldering, 10sec)	+300°C
Total Power Dissipation	300mW
Derate above 25°C	1.7mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
2N3921	Hermetic TO-71	-55°C to +200°C
2N3922	Hermetic TO-71	-55°C to +200°C
X2N3922	Sorted Chip Carriers	-55°C to +200°C



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
I_{GSS}	Gate Reverse Current		-1	nA	$V_{GS} = -30V, V_{DS} = 0$ $T_A = 100^\circ\text{C}$
			-1	μA	
BV_{DGO}	Drain-Gate Breakdown Voltage	50		V	$I_D = 1\mu\text{A}, I_S = 0$
$V_{GS(off)}$	Gate-Source Cutoff Voltage		-3	V	$V_{DS} = 10V, I_D = 1\text{nA}$
V_{GS}	Gate-Source Voltage	-0.2	-2.7	V	$V_{DS} = 10V, I_D = 100\mu\text{A}$
I_G	Gate Operating Current		-250	pA	$V_{DG} = 10V, I_D = 700\mu\text{A}$ $T_A = 100^\circ\text{C}$
			-25	nA	
I_{DSS}	Saturation Drain Current (Note 1)	1	10	mA	$V_{DS} = 10V, V_{GS} = 0$
g_{fs}	Common-Source Forward Transconductance (Note 2)	1500	7500	μS	$V_{DS} = 10V, V_{GS} = 0$ $f = 1\text{kHz}$
g_{os}	Common-Source Output Conductance		35		
C_{iss}	Common-Source Input Capacitance (Note 3)		18	pF	$f = 1\text{MHz}$
C_{rss}	Common-Source Reverse Transfer Capacitance (Note 3)		6		
g_{fs}	Common-Source Forward Transconductance	1500		μS	$V_{DG} = 10V, I_D = 700\mu\text{A}$ $f = 1\text{kHz}$
g_{oss}	Common-Source Output Conductance		20		
NF	Spot Noise Figure (Note 3)		2	dB	$V_{DS} = 10V, V_{GS} = 0$ $f = 1\text{kHz}, R_G = 1\text{meg}\Omega$

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MATCHING CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	2N3921		2N3922		UNITS	TEST CONDITIONS	
		MIN	MAX	MIN	MAX			
$ V_{GS1} - V_{GS2} $	Differential Gate-Source Voltage		5		5	mV	$V_{DG} = 10\text{V}$ $I_D = 700\mu\text{A}$	
$\frac{\Delta V_{GS1} - V_{GS2} }{\Delta T}$	Gate-Source Differential Voltage Change with Temperature		10		25	$\mu\text{V}/^\circ\text{C}$		$T_A = 0^\circ\text{C}$ $T_B = 100^\circ\text{C}$
g_{fs1}/g_{fs2}	Transconductance Ratio	0.95	1.0	0.95	1.0			f = 1kHz

- NOTES:**
1. Per transistor.
 2. Pulse test duration = 2 ms.
 3. For design reference only, not 100% tested.